Innovating Energy Technology

FMV60N280S2HF

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FUJI POWER MOSFET

Super J MOS® S2 series

N-Channel enhancement mode power MOSFET

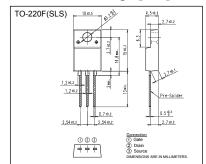
Features

Pb-free lead terminal RoHS compliant uses Halogen-free molding compound

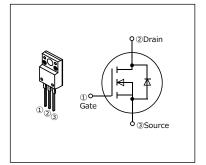
Applications

For switching

Outline Drawings [mm]



Equivalent circuit schematic



■ Absolute Maximum Ratings at T_c=25°C (unless otherwise specified)

Parameter	Symbol	Characteristics	Unit	Remarks
Duain Sauraa Valtana	V DS	600	V	
Drain-Source Voltage	V _{DSX}	600	V	V _{GS} =-30V
Operation and Description Comments	,	13	Α	Tc=25°C Note*1,2
Continuous Drain Current	l _D	8.2	Α	T _c =100°C Note*1,2
Pulsed Drain Current	I DP	41.6	Α	Note *2
Gate-Source Voltage	V GS	±30	V	
Non-Repetitive Maximum Avalanche Current	I AS	1.5	А	Note *2
Non-Repetitive Maximum Avalanche Energy	E AS	468	mJ	Note *3
Maximum Drain-Source dV/dt	dV _{DS} /dt	50	V/ns	V _{DS} ≤ 600V
Continuous	,	13	Α	Tc=25°C Note*1,2
Diode Forward Current	I SD	8.2	Α	Tc=100°C Note*1,2
Pulsed Diode Forward Current	I SDP	41.6	Α	Note *2
Peak Diode Recovery dV/dt	dV/dt	15	V/ns	Note *5
Peak Diode Recovery -di/dt	-di/dt	100	A/µs	Note *6
Maying Days Dissipation	Б	2.16	10/	<i>T</i> ₂=25°C
Maximum Power Dissipation	P_{D}	26	W	<i>T</i> c=25°C
Operating and Storage Temperature range	T ch	150	°C	
	T _{stg}	-55 to +150	°C	
Isolation Voltage	Viso	2	kVrms	t=60sec, f=60Hz

Note *1: Maximum duty cycle D=0.65
Note *2: Limited by maximum channel temperature.
Note *3: T_{ch}≤150°C, See Fig.1 and Fig.2
Note *4: Starting T_{ch}=25°C, I_{AS}=0.9A, L=1.06H, V_{DD}=60V, R_G=50Ω, See Fig.1 and Fig.2

E_{AS} limited by maximum channel temperature and avalanche current.

Note *5 : Iso≤10.4A, -di/dts100A/µs, Vos peak≤ 600V, 7ch≤150°C.

Note *6 : Iso≤10.4A, dV/dt≤15V/ns, Vos peak≤ 600V, 7ch≤150°C.

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■ Electrical Characteristics at *T*_c=25°C (unless otherwise specified) • Static Ratings

Parameter	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA		600	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =150μA		2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I DSS	V _{DS} =600V V _{GS} =0V	T _{ch} =25°C	-	-	25	μΑ
		V _{DS} =480V V _{GS} =0V	T _{ch} =125°C	-	-	250	
Gate-Source Leakage Current	I GSS	V _{DS} =0V V _{GS} = ± 30V		-	10	100	nA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V I _D =5.2A		-	0.248	0.280	Ω
Gate resistance	R _G	f=1MHz, open drain		-	12.7	-	Ω

• Dynamic Ratings

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	g fs	V _{DS} =25V I _D =5.2A	4.7	9.5	-	S
Input Capacitance	Ciss	V _{DS} =400V	-	790	-	
Output Capacitance	Coss	V _{GS} =0V	-	22	-	
Reverse Transfer Capacitance	Crss	f=250kHz	-	3.5	-	
Effective output capacitance, energy related (Note *7)	C _{o(er)}	V _{DS} =0400V V _{GS} =0V	-	53	-	pF
Effective output capacitance, time related (Note *8)	C _{o(tr)}	V _{DS} =0400V V _{GS} =0V I _D =constant	-	183	-	
Turn-On Time	t _{d(on)}	V _{DD} =400V, V _{GS} =10V	-	15	-	
Turri-Ori Tillie	t r	I_0 =5.2A, R_0 =18 Ω See Fig.3 and Fig.4	-	28	-	no
Turn-Off Time	t _{d(off)}		-	95	-	ns
Turn-On Time	t f		-	21	-	
Total Gate Charge	Q _G		-	33	-	
Gate-Source Charge	Q _{GS}	V _{DD} =400V, V _{GS} =10V I _D =10.4A See Fig.5	-	11	-	nC
Gate-Drain Charge	Q _{GD}		-	9	-	nC
Drain-Source crossover Charge	Qsw		-	7	-	

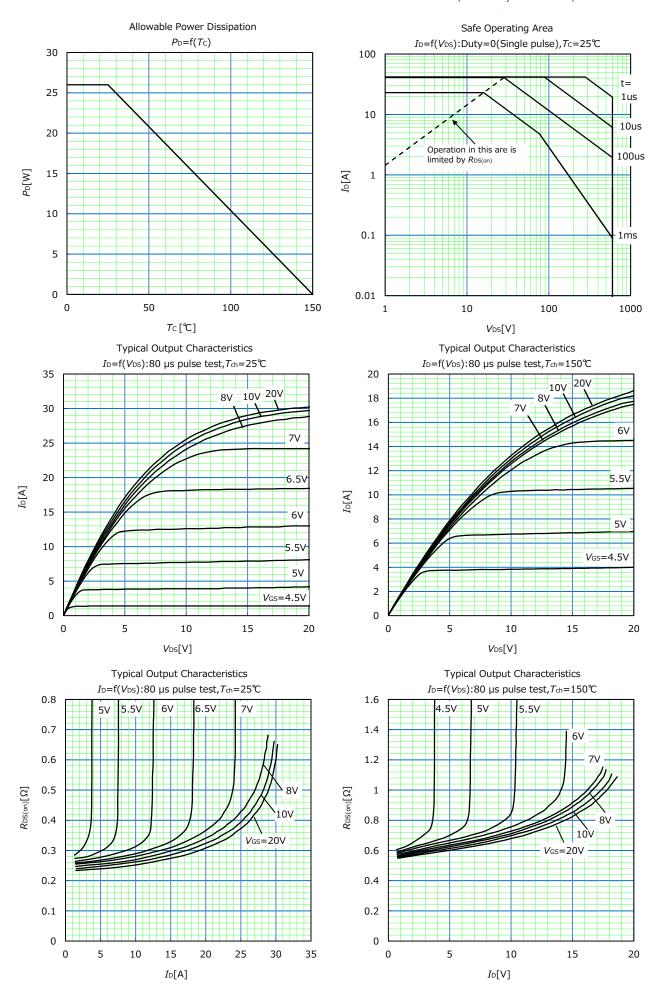
Note *7 : $C_{0(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{Ds} is rising from 0 to 400V. Note *8 : $C_{o(er)}$ is a fixed capacitance that gives the same charging times as C_{oss} while V_{Ds} is rising from 0 to 400V.

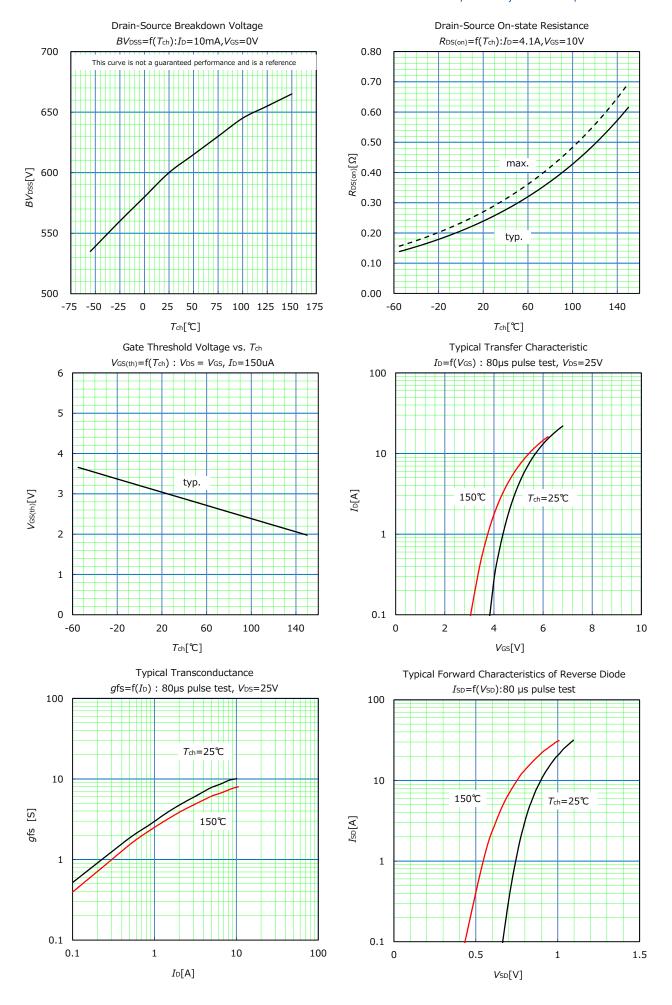
• Reverse Diode

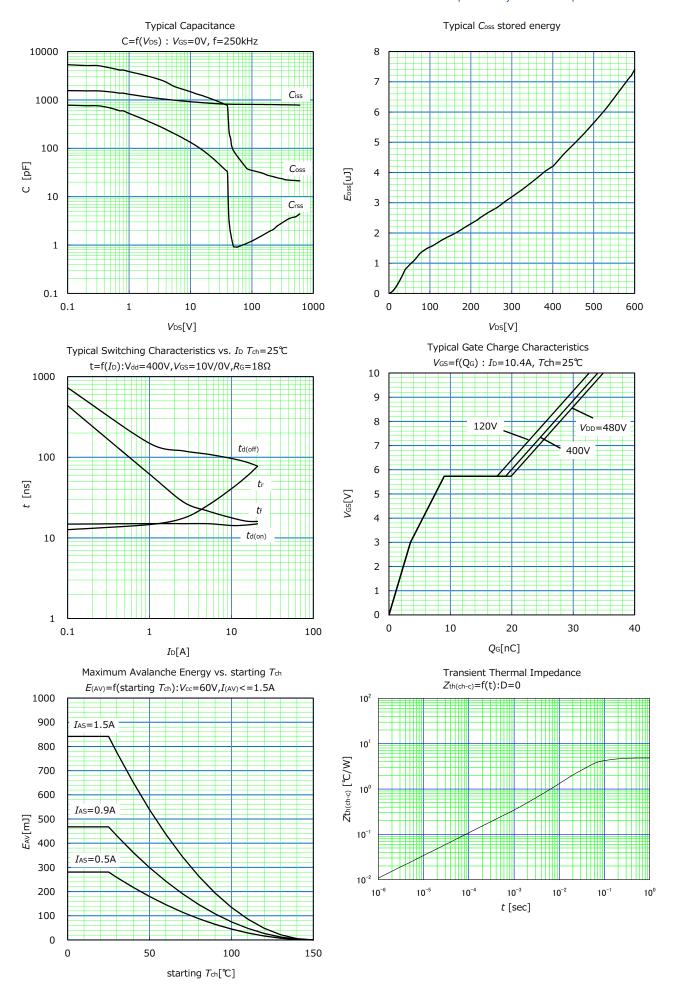
Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode Forward On-Voltage	V _{SD}	I _{SD} =10.4A, V _{SS} =0V T _{ch} =25°C	-	0.95	1.35	V
Reverse Recovery Time	t rr	- V _{DD} =400V, I _{SD} =10.4A -di/dt=100A/μs Τ _{ch} =25°C See Fig.6 and Fig.7	-	290	1	ns
Reverse Recovery Charge	Qrr		-	2.9	-	μC
Peak Reverse Recovery Current	I rp		-	20.5	-	А

■ Thermal Resistance

Parameter	Symbol	min.	typ.	max.	Unit
Channel to Case	Rth(ch-c)	-	-	4.808	°C/W
Channel to Ambient	Rth(ch-a)	-	-	58	°C/W







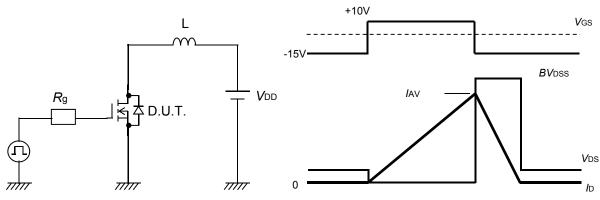


Fig.1 Avalanche Test circuit

Fig.2 Operating waveforms of Avalanche Test

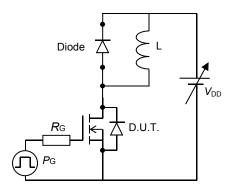


Fig.3 Switching Test circuit

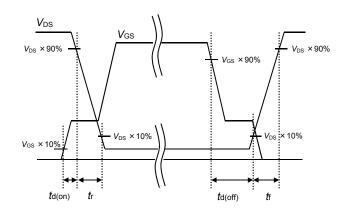


Fig.4 Operating waveform of Switching Test

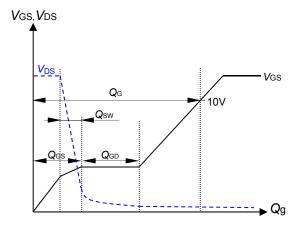


Fig.5 Operating waveform of Gate charge Test

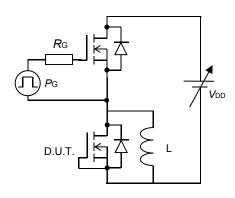


Fig.6 Reverse recovery Test circuit

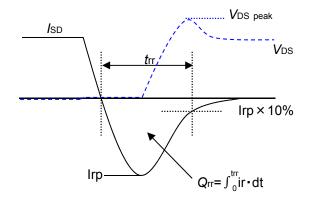
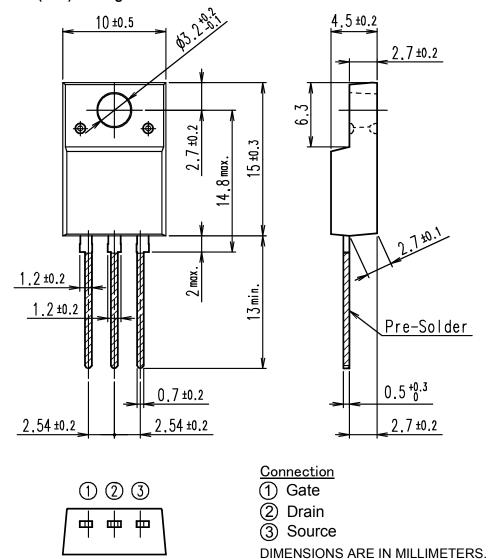
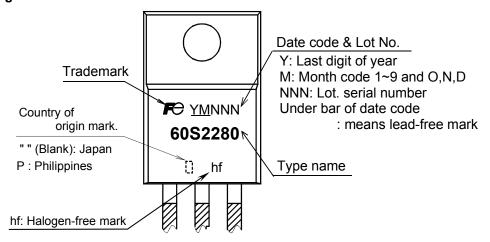


Fig.7 Operating waveform of Reverse recovery Test

Outview: TO-220F(SLS) Package



Marking



^{*} The font (font type,size) and the trademark-size might be actually different.

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